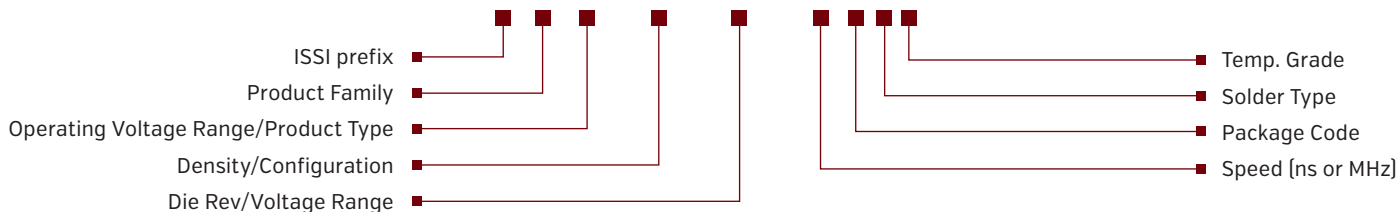




SRAM Part Decoder

IS 61 WV 12816 DBLL - 10 T L I



■ SRAM Product Family

- 61/63 = High Speed
- 62 = Low Power
- 64 = Automotive High Speed
- 65 = Automotive Low Power
- 66 = Pseudo SRAM
- 67 = Automotive PSRAM

■ Density/Configuration

- Example:
- 25636 = 256Kx36
 - 51216 = 512Kx16
 - 1M36 = 1Mx36

■ Die Rev/Voltage Range

- Die Rev**
- Blank-Z
- Voltage Range (WV)**
- ALL = 1.65V to 2.2V
 - BLL = 2.2V [2.4V/2.5V] to 3.6V

■ Operating Voltage Range/Product Type

- Asynchronous SRAM**
- C = 5V
 - LV = 3.3V
 - WV = Wide Voltage Range
- Synchronous SRAM**
- P = Pipeline, F = Flowthrough
 - NLP/NLF/NVP/NVF = No-Wait Option
 - LP/LF: Vcc = 3.3V, VccQ = 3.3V/2.5V
 - VP/VF: Vcc = 2.5V, VccQ = 2.5V
 - QD = QUAD, DD = DDR-II
 - Common I/O: Vcc = 1.8V, VccQ = 1.8V/1.5V

■ Temp. Grade

- Blank = Commercial Grade [0C to +70°C]
- I = Industrial Grade [-40C to +85°C]
- A1 = Automotive Grade [-40C to +85°C]
- A2 = Automotive Grade [-40C to +105°C]
- A3 = Automotive Grade [-40C to +125°C]

■ Solder Type

- Blank = SnPb
- L = Lead-free [RoHS Compliant]

■ Speed [ns or MHz]

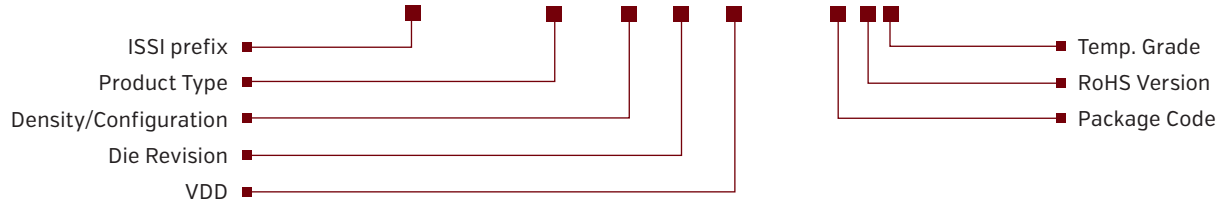
- Example:
- 8 = 8ns
 - 200 = 200MHz

■ Package Code

- B, B1, B2, B3 = BGA
- CT = Copper TSOP
- H = sTSOP
- J = 300-mil SOJ
- K = 400-mil SOJ
- LQ = LQFP
- M, M3, = BGA
- Q = SOP
- T/T2 = TSOP
- TQ = TQFP
- U = SOP

PSRAM Part Decoder

IS 66/67 WVE 4M16 x BLL - 70 B L I



PSRAM Product Type

Blank = Standard Asynch PSRAM
E = Asynch/Page PSRAM
C = Cellular RAM 1.5
D = Cellular RAM 2.0

Density/Configuration

51216 = 8Mb /512K x16
1M16 = 16Mb /1M x16
2M16 = 32Mb /2M x16
4M16 = 64Mb /4M x16

Die Rev

Die Rev
VDD
ALL = 1.8V
BLL = 3V

Package Code

B = BGA
T = TSOP

Temperature Range

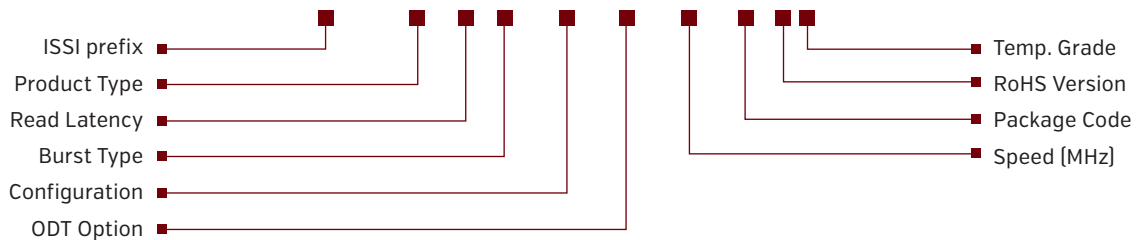
I = Industrial [-40°C to 85°C]
A1 = Automotive [-40°C to 85°C]

RoHS Version

Blank = Leaded
L = Lead-free

QUAD/P, DDR-II/P Part Decoder

IS 61 QDP 2 B4 4M18 A1 - 333 M3 L I



Product Type

QD = QUAD
QDP = QUADP
DD = DDR-II, Common I/O
DDP = DDR-IIP, Common I/O

Configuration

51236 = 512Kb x 36
1M18 = 1Mb x 18
1M36 = 1Mb x 36
2M18 = 2Mb x 18
2M36 = 2Mb x 36
4M18 = 4Mb x 18

Read Latency (RL):

For QUAD/DDR-II devices:
Blank = 1.5 clock cycles
For QUADP/DDR-IIP devices:
Blank = 2.5 clock cycles
2 = 2.0 clock cycles

Burst Type:

B2 = Burst 2
B4 = Burst 4

ODT Option (if supported):

A: No ODT
A1: ODT Option 1
If ODT = HIGH or floating, a high range termination resistance is selected.
If ODT = LOW, a low range termination resistance is selected.
A2: ODT Option 2
If ODT = HIGH, a high range termination resistance is selected.
If ODT = LOW or floating, ODT is disabled

Speed

Example
250 = 250MHz

Package Code

B4 = 165 ball BGA (13 x 15 mm)
M3 = 165-ball BGA (15 x 17 mm)

RoHS Version

Blank = Leaded
L = Lead-free

Temperature Range

Blank = Commercial (0C to 70°C)
I = Industrial [-40C to 85°C]